

In the Claims:

The claims are as follows.

1-10. (Canceled)

11. (Original) A method for forming a multilayered stack, comprising the steps of:

 forming a first dielectric layer that includes a first liquid crystal polymer (LCP) dielectric material, wherein a first electrical circuitization is on and in direct mechanical contact with a surface of the first dielectric layer;

 forming a second dielectric layer that includes a second LCP dielectric material, wherein a first electrically conductive plug includes a first electrically conductive material and extends through a thickness of the second dielectric layer, wherein a second electrical circuitization is on and in direct mechanical contact with a surface of the second dielectric layer, wherein the second electrical circuitization is in direct mechanical and electrical contact with a first end of the first electrically conductive plug;

 fluxlessly soldering the first electrically conductive plug to the first electrical circuitization; and

 subjecting the first dielectric layer, the second dielectric layer, and the first electrical circuitization to a temperature less than the lowest nematic-to-isotropic transition temperature of the first and second LCP dielectric materials, for a dwell time and at an elevated pressure that is sufficient to cause the first and second LCP dielectric materials to plastically deform and directly bond the second dielectric layer to the first dielectric layer and directly bond the second dielectric

layer to the first electrical circuitization with no extrinsic adhesive material disposed between the second dielectric layer and the first dielectric layer and with no extrinsic adhesive material disposed between the second dielectric layer and the first electrical circuitization.

12. (Original) The method of claim 11, wherein the step of subjecting the first dielectric layer is performed after the fluxlessly soldering step.

13. (Original) The method of claim 11, wherein the step of subjecting the first dielectric layer is performed simultaneous with the fluxlessly soldering step.

14. (Original) The method of claim 11, wherein the polymer chain structure and associated directional orientation of the first and second LCP dielectric materials remains essentially unchanged throughout the dwell time.

15. (Original) The method of claim 11, wherein the coefficient of thermal expansion (CTE) of the first and second LCP dielectric materials remains essentially unchanged throughout the dwell time.

16. (Original) The method of claim 11, wherein the elevated pressure is in a range of about 1000 psi to about 3000 psi.

17. (Original) The method of claim 11, wherein the dwell time is at least about 2 minutes.

18. (Original) The method of claim 11, wherein the first LCP dielectric material and the second LCP dielectric material are a same LCP dielectric material.

19. (Original) The method of claim 11, wherein the first LCP dielectric material and the second LCP dielectric material are different LCP dielectric materials.

20. (Original) The method of claim 11, wherein the fluxlessly soldering step leaves a void volume between the first and second LCP dielectric layers, and wherein the subjecting step causes the void volume to be filled by at least one of the first and second LCP dielectric materials.